

New Jersey Semi-Conductor Products, Inc.

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MUR1610CT, MUR1615CT, MUR1620CT, MUR1640CT, MUR1660CT

SWITCHMODE™ Power Rectifiers

These state-of-the-art devices are a series designed for use in switching power supplies, inverters and as free wheeling diodes.

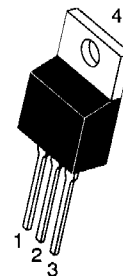
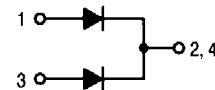
Features

- Ultrafast 35 and 60 Nanosecond Recovery Times
- 175°C Operating Junction Temperature
- Popular TO-220 Package
- Epoxy Meets UL 94 V-0 @ 0.125 in
- High Temperature Glass Passivated Junction
- High Voltage Capability to 600 V
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating @ Both Case and Ambient Temperatures
- Pb-Free Packages are Available*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
260°C Max. for 10 Seconds

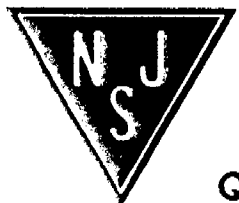
ULTRAFAST RECTIFIERS 16 AMPERES, 100-600 VOLTS



TO-220AB

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors



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MAXIMUM RATINGS

Rating	Symbol	MUR16					Unit
		10CT	15CT	20CT	40CT	60CT	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	150	200	400	600	V
Average Rectified Forward Current Total Device, (Rated V_R), $T_C = 150^\circ\text{C}$	$I_{F(AV)}$ Per Leg Total Device	8.0 16					A
Peak Rectified Forward Current (Rated V_R , Square Wave, 20 kHz), $T_C = 150^\circ\text{C}$	I_{FM} Per Diode Leg	16					A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	100					A
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	-65 to +175					$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS (Per Diode Leg)

Parameter	Symbol	Value		Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	2.0	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	1620	1640	1660	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 8.0\text{ A}$, $T_C = 150^\circ\text{C}$) ($I_F = 8.0\text{ A}$, $T_C = 25^\circ\text{C}$)	V_F	0.895 0.975	1.00 1.30	1.20 1.50	V
Maximum Instantaneous Reverse Current (Note 1) (Rated DC Voltage, $T_C = 150^\circ\text{C}$) (Rated DC Voltage, $T_C = 25^\circ\text{C}$)	i_R	250 5.0	500 10		μA
Maximum Reverse Recovery Time ($I_F = 1.0\text{ A}$, $di/dt = 50\text{ A}/\mu\text{s}$) ($I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{REC} = 0.25\text{ A}$)	t_{rr}	35 25	60 50		ns

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$